



R U N A U

Jiangsu Runau Electronics Manufacturing Co.,Ltd

ZP800-Rectifier Diode

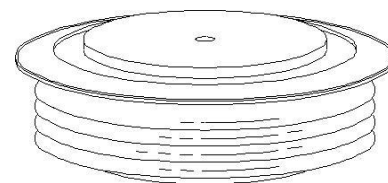
600 - 1600 V_{RRM}

GENERAL PURPOSE HIGH POWER STANDARD RECTIFIER

Features:

- . All diffused structure
- . High surge rating
- . Blocking capability up to 2000 volts
- . Ceramic housing hermetic package
- . Pressure assembled device

ZT30aT



ELECTRICAL CHARACTERISTICS AND RATINGS

Reverse Blocking

Device Type	V _{RRM} (1)	V _{RSM} (1)
ZP800-06	600	800
ZP800-08	800	1000
ZP800-10	1000	1200
ZP800-12	1200	1400
ZP800-14	1400	1600
ZP800-16	1600	1800

V_{RRM} = Repetitive peak reverse voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I _{RRM}	2 mA 30 mA (3)
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Notes:

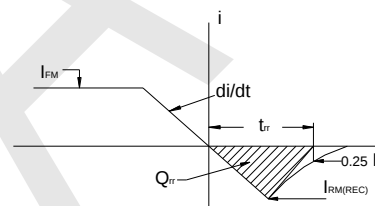
All ratings are specified for T_j=25 °C, unless otherwise stated

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +175 °C.

(2) 10 msec. max. pulse width

(3) Maximum value for T_j = 175 °C.

(4) See parameter definition below :



REVERSE RECOVERY CHARACTERIST

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	I _{F(AV)}		800		A	Sinewave 180°, T _c =100°C
RMS forward current	I _{FRMS}		1250		A	Nominal value
Peak one cycle surge (non repetitive) current	I _{FSM}		8800		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j = 175 °C
I square t	I ² t		38 × 10 ⁴		A ² s	10 msec
Peak forward voltage	V _{FM}		1.30		V	I _{FM} = 1500A; T _j =25°C
Threshold voltage	V _{FO}		0.8		V	T _j =175°C, I=0.5π I _{F(AV)} to 1.5π I _{F(AV)}
Slope resistance	r _F		0.28		mΩ	T _j =175°C, I=0.5π I _{F(AV)} to 1.5π I _{F(AV)}
Reverse Recovery Current (4)	I _{RM(REC)}				A	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}
Reverse Recovery Charge (4)	Q _{rr}			2000	μC	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}
Reverse Recovery Time (4)	t _{rr}				μs	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+175		$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-40	+175		$^{\circ}\text{C}$	
Thermal resistance - junction to case	$R_{\Theta(j-c)}$		0.054		$^{\circ}\text{C/W}$	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta(c-s)}$		0.02		$^{\circ}\text{C/W}$	Double sided cooled
Mounting force	P	9	11	10	kN	
Weight	W			0.08	kg.	

* Mounting surfaces smooth, flat and greaseless

CASE OUTLINE AND DIMENSIONS

